

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S166	13944	455/131.232.1,255,313,323,333,334.ccls. 438/151,163,585,586.ccls. 257/347,401,499,500,501,508,517,518,520,901.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:03
S167	1894	semiconductor with (differential near2 circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:04
S168	22026	substrate same (gate adj electrode) same (drain adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:08
S169	12264	substrate same (gate adj electrode) same (drain adj electrode) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:09
S170	534	(gate adj electrode) with (drain adj electrode) with (resistance resistor) with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:09
S171	7	S167 and S170	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:13
S172	9	semiconductor adj differential adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 16:15
S173	27	S166 and S170	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 17:06

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(semiconductor with (differential adj circuit) with substrate with ("same" near2 (resistance resistor)) with ((collector base) (drain with gate))).clm.	US-PGPUB; USPAT	OR	ON	2006/03/19 17:30
L2	0	(semiconductor with (differential adj circuit) with substrate with ("same" near2 (resistance resistor))).clm.	US-PGPUB; USPAT	OR	ON	2006/03/19 17:31